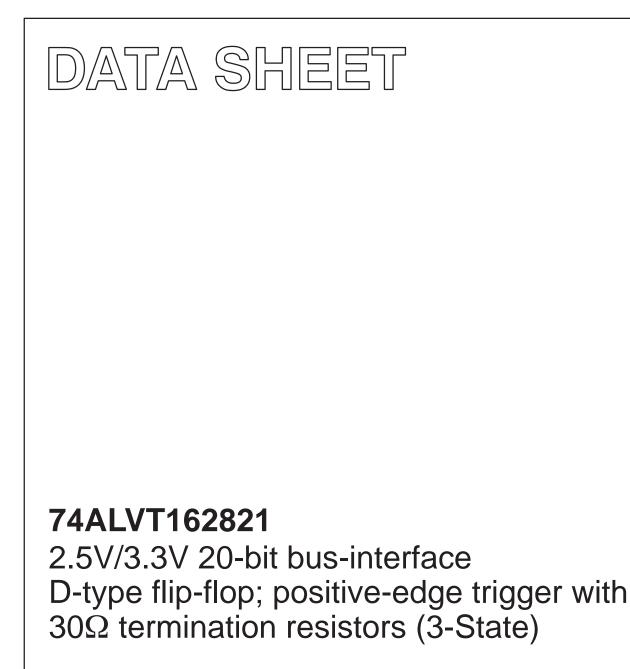
INTEGRATED CIRCUITS



Product specification Supersedes data of 1997 Feb 13 IC23 Data Handbook

1998 Oct 02



74ALVT162821

FEATURES

- Outputs include series resistance of 30Ω making external termination resistors unnecessary
- 20-bit positive-edge triggered register
- 5V I/O Compatible
- Multiple V_{CC} and GND pins minimize switching noise
- Live insertion/extraction permitted
- Power-up reset
- Power-up 3-State
- Output capability +12mA/-12mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Bus hold data inputs eliminate the need for external pull-up resistors to hold unused inputs

DESCRIPTION

The 74ALVT162821 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive. It is designed for V_{CC} operation at 2.5V or 3.3V with I/O compatibility to 5V.

The 74ALVT162821 has two 10-bit, edge triggered registers, with each register coupled to a 3-State output buffer. The two sections of each register are controlled independently by the clock (nCP) and Output Enable ($n\overline{OE}$) control gates.

Each register is fully edge triggered. The state of each D input, one set-up time before the Low-to-High clock transition, is transferred to the corresponding flip-flop's Q output.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors.

The active Low Output Enable ($n\overline{OE}$) controls all ten 3-State buffers independent of the register operation. When $n\overline{OE}$ is Low, the data in the register appears at the outputs. When $n\overline{OE}$ is High, the outputs are in high impedance "off" state, which means they will neither drive nor load the bus.

The 74ALVT162821 is designed with 30Ω series resistance in both High and Low output stages. This design reduces the line noise in applications such as memory address drivers, clock drivers and bus receivers/transmitters. The series termination resistors reduce overshoot and undershoot and are ideal for driving memory arrays.

QUICK REFERENCE DATA

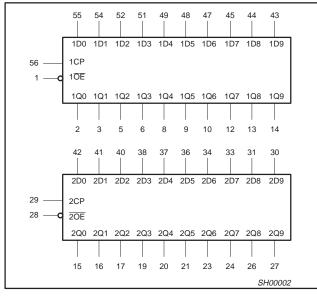
SYMBOL	PARAMETER	CONDITIONS	TYPI	UNIT	
STMBOL	$T_{amb} = 25^{\circ}C$		2.5V	3.3V	UNIT
t _{PLH} t _{PHL}	Propagation delay nCP to nQ	$C_L = 50 pF$	4.4 3.8	3.2 3.2	ns
C _{IN}	Input capacitance	$V_I = 0V \text{ or } V_{CC}$	3	3	pF
C _{OUT}	Output capacitance	$V_{O} = 0 \text{ or } V_{CC}$	9	9	pF
I _{CCZ}	Total supply current	Outputs disabled	40	70	μΑ

ORDERING INFORMATION

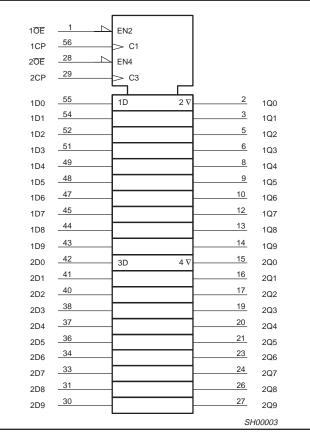
PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
56-Pin Plastic SSOP Type III	–40°C to +85°C	74ALVT162821 DL	AV162821 DL	SOT371-1
56-Pin Plastic TSSOP Type II	–40°C to +85°C	74ALVT162821 DGG	AV162821 DGG	SOT364-1

74ALVT162821

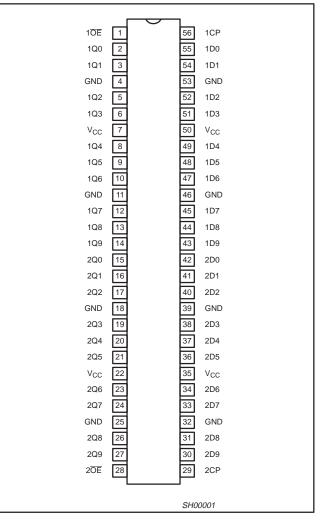
LOGIC SYMBOL



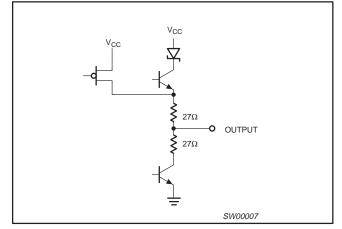
LOGIC SYMBOL (IEEE/IEC)



PIN CONFIGURATION



SCHEMATIC OF EACH OUTPUT



74ALVT162821

PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
55, 54, 52, 51, 49, 48, 47, 45, 44, 43, 42, 41, 40, 38, 37, 36, 34, 33, 31, 30	1D0 - 1D9 2D0 - 2D9	Data inputs
2, 3, 5, 6, 8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21, 23, 24, 26, 27	1Q0 - 1Q9 2Q0 - 2Q9	Data outputs
1, 28	1 <u>0E</u> , 2 <u>0E</u>	Output enable inputs (active-Low)
56, 29	1CP, 2CP	Clock pulse inputs (active rising edge)
4, 11, 18, 25, 32, 39, 46, 53	GND	Ground (0V)
7, 22, 35, 50	V _{CC}	Positive supply voltage

LOGIC DIAGRAM

FUNCTION TABLE

I	NPUTS	5	INTERNAL	OUTPUTS	OPERATING
nOE	nCP	nDx	REGISTER	nQ0 - nQ9	MODE
L	$\stackrel{\wedge}{\leftarrow}$	l h	L H	L H	Load and read register
L	1	Х	NC	NC	Hold
H H	$\stackrel{}{\uparrow}$	X Dn	NC Dn	Z Z	Disable outputs

H = High voltage level

h = High voltage level one set-up time prior to the Low-to-High clock transition

Low voltage level =

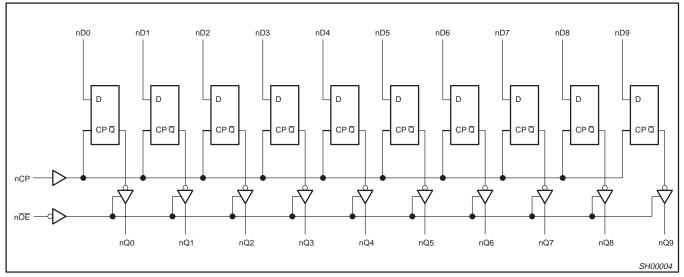
L Low voltage level one set-up time prior to the Low-to-High clock transition L =

NC= No change

Don't care

X = Z = ↑ = ↓ =

High impedance "off" state
Low to High clock transition
Not a Low-to-High clock transition



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ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +4.6	V
I _{IK}	DC input diode current	V ₁ < 0	-50	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{ОК}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	Output in Off or High state	-0.5 to +7.0	V
		Output in Low state	128	
Ιουτ	DC output current	Output in High state	-64	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction

temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	2.5V RAN	GE LIMITS	3.3V RAN	UNIT	
STMBOL		MIN	MAX	MIN	MAX	ONIT
V _{CC}	DC supply voltage	2.3	2.7	3.0	3.6	V
VI	Input voltage	0	5.5	0	5.5	V
V _{IH}	High-level input voltage	1.7		2.0		V
V _{IL}	Input voltage		0.7		0.8	V
I _{OH}	High-level output current		-8		-12	mA
I _{OL}	Low-level output current		12		12	mA
$\Delta t / \Delta v$	Input transition rise or fall rate; Outputs enabled		10		10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	-40	+85	°C

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DC ELECTRICAL CHARACTERISTICS ($3.3V \pm 0.3V$ RANGE)

					LIMITS		
				MIN	TYP ¹	MAX	
VIK	Input clamp voltage	$V_{CC} = 3.0V; I_{IK} = -18mA$			-0.85	-1.2	V
V _{OH}	High-level output voltage	$V_{CC} = 3.0$ to 3.6V; $I_{OH} = -100\mu A$		V _{CC} -0.2	V _{CC}		v
VОН	l ligh-level output voltage	$V_{CC} = 3.0V; I_{OH} = -32mA$		2.0	2.3		v
		V _{CC} = 3.0V; I _{OL} = 100μA			0.07	0.2	
Va	Low-level output voltage	V _{CC} = 3.0V; I _{OL} = 16mA			0.25	0.4	V
VOL	V _{OL} Low–level output voltage	V _{CC} = 3.0V; I _{OL} = 32mA			0.3	0.5	v
		$V_{CC} = 3.0V; I_{OL} = 64mA$			0.4	0.55	
V _{RST}	Power-up output low voltage ⁶	$V_{CC} = 3.6V; I_{O} = 1mA; V_{I} = V_{CC} \text{ or GND}$)			0.55	V
		$V_{CC} = 3.6V; V_{I} = V_{CC} \text{ or } GND$	Control pins		0.1	±1	
	Input lookage ourrept	$V_{CC} = 0 \text{ or } 3.6 \text{V}; \text{ V}_{I} = 5.5 \text{V}$			0.1	10	μA
łı	Input leakage current	$V_{CC} = 3.6V; V_{I} = V_{CC}$	Data pins4		0.5	1	
		$V_{CC} = 3.6V; V_{I} = 0V$	Data pins		0.1	-5	
I _{OFF}	Off current	$V_{CC} = 0V$; V_{I} or $V_{O} = 0$ to 4.5V			0.1	±100	μΑ
	Bus Hold current	$V_{CC} = 3V; V_{I} = 0.8V$		75	130		
I _{HOLD}	Data inputs ⁷	$V_{CC} = 3V; V_{I} = 2.0V$		-75	-140		μΑ
		$V_{CC} = 0V$ to 3.6V; $V_{CC} = 3.6V$		±500			
I_{EX}	Current into an output in the High state when $V_O > V_{CC}$	V _O = 5.5V; V _{CC} = 3.0V			10	125	μΑ
I _{PU/PD}	Power up/down 3-State output current ³	$V_{CC} \le 1.2V$; $V_O = 0.5V$ to V_{CC} ; $V_I = GNIOE = Don't$ care	D or V _{CC}		1	±100	μA
I _{OZH}	3-State output High current	$V_{CC} = 3.6V; V_{O} = 3.0V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	5	μA
I _{OZL}	3-State output Low current	$V_{CC} = 3.6V; V_O = 0.5V; V_I = V_{IL} \text{ or } V_{IH}$			0.5	-5	μA
I _{CCH}		V_{CC} = 3.6V; Outputs High, V_{I} = GND or V_{CC} , I_{O} = 0			0.07	0.1	
I _{CCL}	Quiescent supply current	$V_{CC} = 3.6V$; Outputs Low, $V_I = GND$ or V_{CC} , $I_O = 0$			5.1	7	mA
I _{CCZ}	1	$V_{CC} = 3.6V$; Outputs Disabled; $V_I = GNI$	D or V _{CC} , $I_{O} = 0^5$		0.07	0.1	
ΔI_{CC}	Additional supply current per input pin ²	$V_{CC} = 3V$ to 3.6V; One input at V_{CC} -0.6 Other inputs at V_{CC} or GND	SV,		0.04	0.4	mA

NOTES:

1. All typical values are at $V_{CC} = 3.3V$ and $T_{amb} = 25^{\circ}C$. 2. This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND 3. This parameter is valid for any V_{CC} between 0V and 1.2V with a transition time of up to 10msec. From $V_{CC} = 1.2V$ to $V_{CC} = 3.3V \pm 0.2V$ a transition time of 100 μ sec is permitted. This parameter is valid for T_{amb} = 25°C only.

4. Unused pins at V_{CC} or GND.

I_{CCZ} is measured with outputs pulled up to V_{CC} or pulled down to ground.
For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

7. This is the bus hold overdrive current required to force the input to the opposite logic state.

AC CHARACTERISTICS (3.3V \pm 0.3V RANGE) GND = 0V; t_R = t_F = 2.5ns; C_I = 50pF; R_I = 500Ω; T_{amb} = -40°C to +85°C.

SYMBOL	PARAMETER	WAVEFORM	T _{an}	nb = -40 to +8 V _{CC} = +3.3V	5°C	UNIT
			MIN	TYP	MAX	
f _{MAX}	Maximum clock frequency	1	150			MHz
t _{PLH} t _{PHL}	Propagation delay nCP to nQx	1	1.0 1.0	3.2 3.2	5.0 4.7	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	3 4	1.0 0.5	3.4 2.3	5.6 3.7	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	3 4	1.5 1.5	3.7 3.0	5.4 4.3	ns

NOTE:

1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

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AC SETUP REQUIREMENTS (3.3V \pm 0.3V RANGE) GND = 0V, t_R = t_F = 2.5ns, C_L = 50pF, R_L = 500 Ω

	PARAMETER		LIN		
SYMBOL		WAVEFORM	T _{amb} = -40 to +85°C V _{CC} = +3.3V ±0.3V		UNIT
			MIN	TYP	
t _s (H) t _s (L)	Setup time, High or Low nDx to nCP	1	1.5 1.5	0.1 0.1	ns
t _h (H) t _h (L)	Hold time, High or Low nDx to nCP	2	0.5 0.5	0.1 0.1	ns
t _w (H) t _w (L)	nCP pulse width High or Low	2	1.5 1.5		ns

DC ELECTRICAL CHARACTERISTICS (2.5V ± 0.2V RANGE)

					LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS		Temp = ·	-40°C to	+85°C	UNIT
				MIN	TYP ¹	MAX	
V _{IK}	Input clamp voltage	$V_{CC} = 2.3V; I_{IK} = -18mA$			-0.85	-1.2	V
Voh	High-level output voltage	$V_{CC} = 2.3$ to 3.6V; $I_{OH} = -100\mu A$		V _{CC} -0.2	V _{CC}		V
VOH	nigh-level output voltage	$V_{CC} = 2.3V; I_{OH} = -8mA$		1.8	2.1		v
		$V_{CC} = 2.3V; I_{OL} = 100\mu A$			0.07	0.2	
V _{OL}	Low-level output voltage	$V_{CC} = 2.3V; I_{OL} = 24mA$			0.3	0.5	V
		$V_{CC} = 2.3V; I_{OL} = 8mA$				0.4	
V _{RST}	Power-up output low voltage ⁷	V_{CC} = 2.7V; I_{O} = 1mA; V_{I} = V_{CC} or GND				0.55	V
		$V_{CC} = 2.7V; V_I = V_{CC}$ or GND	Control pins		0.1	±1	
L 1.	Input leakage current	$V_{CC} = 0 \text{ or } 2.7 \text{V}; \text{ V}_{\text{I}} = 5.5 \text{V}$			0.1	10	μA
¹ 1	ij input leakage current	$V_{CC} = 2.7V; V_{I} = V_{CC}$	Data pins4		0.1	1	μΑ
		$V_{CC} = 2.7V; V_I = 0$	Data pins		0.1	-5	
I _{OFF}	Off current	$V_{CC} = 0V$; V_I or $V_O = 0$ to 4.5V			0.1	±100	μΑ
I _{HOLD}	Bus Hold current	$V_{CC} = 2.3V; V_I = 0.7V$			90		μA
	Data inputs ⁶	V _{CC} = 2.3V; V _I = 1.7V			-10		μΑ
I _{EX}	Current into an output in the High state when $V_O > V_{CC}$	V _O = 5.5V; V _{CC} = 2.3V			10	125	μΑ
I _{PU/PD}	Power up/down 3-State output current ³	$V_{CC} \le 1.2$ V; $V_O = 0.5$ V to V_{CC} ; $V_I = GND OE/OE = Don't care$) or V _{CC}		1	±100	μA
I _{OZH}	3-State output High current	$V_{CC} = 2.7V; V_{O} = 2.3V; V_{I} = V_{IL} \text{ or } V_{IH}$			0.5	5	μA
I _{OZL}	3-State output Low current	$V_{CC} = 2.7V; V_{O} = 0.5V; V_{I} = V_{IL} \text{ or } V_{IH}$		1	0.5	-5	μA
I _{ССН}		V_{CC} = 2.7V; Outputs High, V_{I} = GND or V_{CC} , I_{O} = 0		1	0.04	0.1	
I _{CCL}	Quiescent supply current	V_{CC} = 2.7V; Outputs Low, V_{I} = GND or V_{CC} , I_{O} = 0			2.3	4.5	mA
I _{CCZ}	1	$V_{CC} = 2.7V$; Outputs Disabled; $V_I = GND \text{ or } V_{CC}$, $I_O = 0^5$			0.04	0.1	
ΔI _{CC}	Additional supply current per input pin ²	V_{CC} = 2.3V to 2.7V; One input at V_{CC} -0. Other inputs at V_{CC} or GND	6V,		0.04	0.4	mA

NOTES:

1. All typical values are at $V_{CC} = 2.5V$ and $T_{amb} = 25^{\circ}C$. 2. This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND

3. This parameter is valid for any V_{CC} between 0V and 1.2V with a transition time of up to 10msec. From V_{CC} = 1.2V to V_{CC} = 2.5V \pm 0.3V a transition time of 100µsec is permitted. This parameter is valid for T_{amb} = 25°C only.

4. Unused pins at V_{CC} or GND.

I_{CCZ} is measured with outputs pulled up to V_{CC} or pulled down to ground.
Not guaranteed.

7. For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

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AC CHARACTERISTICS (2.5V ±0.2V RANGE)

GND = 0V; $t_R = t_F = 2.5 \text{ ns}$; $C_L = 50 \text{ pF}$; $R_L = 500 \Omega$; $T_{amb} = -40^{\circ} \text{C}$ to +85°C.

				LIMITS			
SYMBOL	PARAMETER	PARAMETER WAVEFORM		T _{amb} = -40 to +85°C V _{CC} = +2.5V ±0.2V			
			MIN	ТҮР	MAX		
f _{MAX}	Maximum clock frequency	1	150			MHz	
t _{PLH} t _{PHL}	Propagation delay nCP to nQx	1	1.0 1.0	4.4 3.8	7.0 6.4	ns	
t _{PZH} t _{PZL}	Output enable time to High and Low level	3 4	1.5 1.0	4.6 2.8	7.5 4.6	ns	
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	3 4	1.5 1.0	3.5 3.7	5.5 5.7	ns	

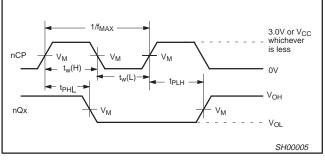
1. All typical values are at $V_{CC} = 3.3V$ and $T_{amb} = 25^{\circ}C$.

AC SETUP REQUIREMENTS (2.5V \pm 0.2V RANGE) GND = 0V, t_{R} = t_{F} = 2.5ns, C_{L} = 50pF, R_{L} = 500 Ω

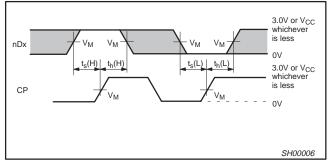
			LIN	NITS	
SYMBOL	PARAMETER	WAVEFORM	T _{amb} = -40 to +85°C V _{CC} = +2.5 ±0.2V		UNIT
			MIN	TYP	
t _s (H) t _s (L)	Setup time, High or Low nDx to nCP	1	1.5 2.0	0.1 0.5	ns
t _h (H) t _h (L)	Hold time, High or Low nDx to nCP	2	0.3 0.5	-0.5 -0.1	ns
t _w (H) t _w (L)	nCP pulse width High or Low	2	1.5 1.5		ns

AC WAVEFORMS

 $\begin{array}{l} {\sf V}_{\sf M} = 1.5{\sf V} \mbox{ at } {\sf V}_{\sf CC} \geq 3.0{\sf V}; \mbox{ } {\sf V}_{\sf M} = {\sf V}_{\sf CC}/2 \mbox{ at } {\sf V}_{\sf CC} \leq 2.7{\sf V} \\ {\sf V}_{\sf X} = {\sf V}_{\sf OL} + 0.3{\sf V} \mbox{ at } {\sf V}_{\sf CC} \geq 3.0{\sf V}; \mbox{ } {\sf V}_{\sf X} = {\sf V}_{\sf OL} + 0.15{\sf V} \mbox{ at } {\sf V}_{\sf CC} \leq 2.7{\sf V} \\ {\sf V}_{\sf Y} = {\sf V}_{\sf OH} - 0.3{\sf V} \mbox{ at } {\sf V}_{\sf CC} \geq 3.0{\sf V}; \mbox{ } {\sf V}_{\sf Y} = {\sf V}_{\sf OH} - 0.15{\sf V} \mbox{ at } {\sf V}_{\sf CC} \leq 2.7{\sf V} \end{array}$

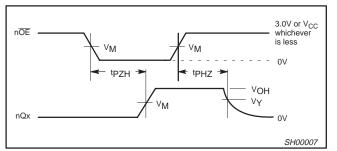


Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock frequency

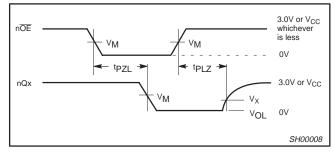


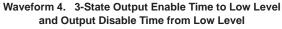
Waveform 2. Data Setup and Hold Times

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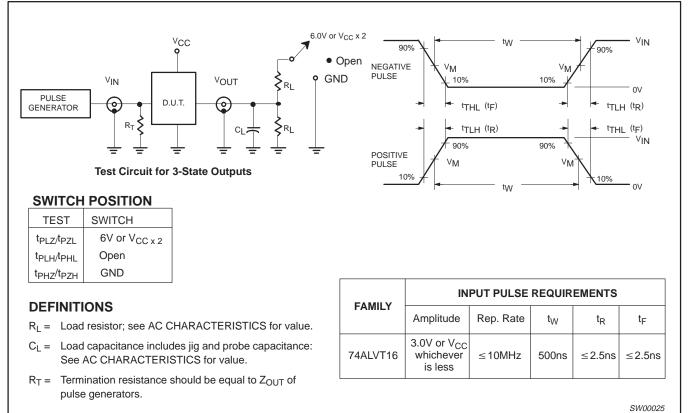




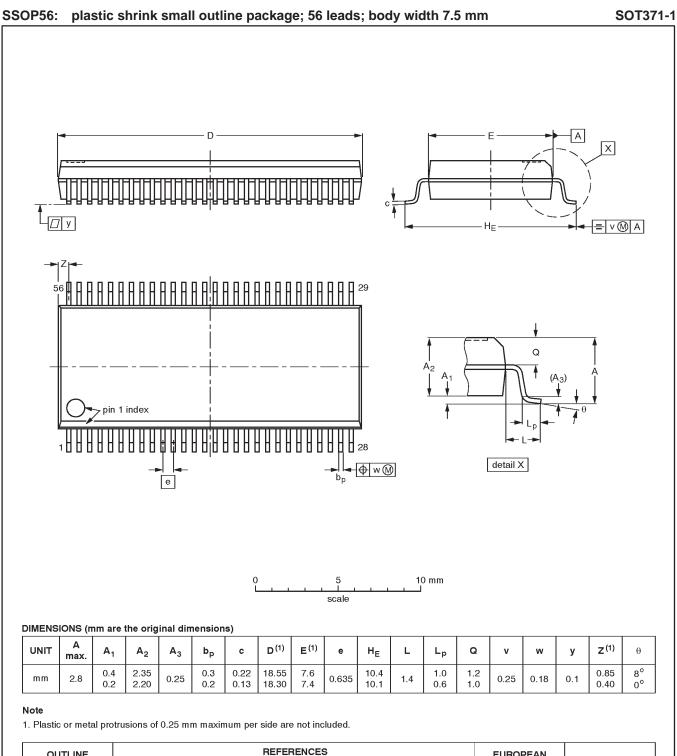




TEST CIRCUIT AND WAVEFORM

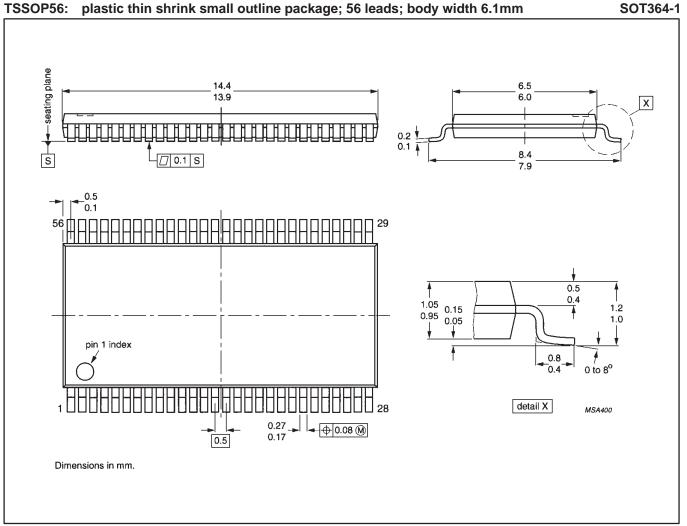


74ALVT162821



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	
SOT371-1		MO-118AB			-93-11-02- 95-02-04

74ALVT162821



Product specification

74ALVT162821

Data sheet status

Data sheet status	Product status	Definition ^[1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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